

60\$ 3/\$676,& ,&25(&7,) ,(56)

)(\$785(6

"Plastic package has Underwriters Laboratory

Flammability Classification 94V-O Utilizing

"For surface mounted applications

"Metal silicon junction,majority carrier conduction

"Low power loss,high efficiency

"Built-in strain relief,ideal for automated placement

"High forward surge current capability

"High temperature soldering guaranteed:260 /10 seconds at
terminals"Component in accordance to RoHS
(8

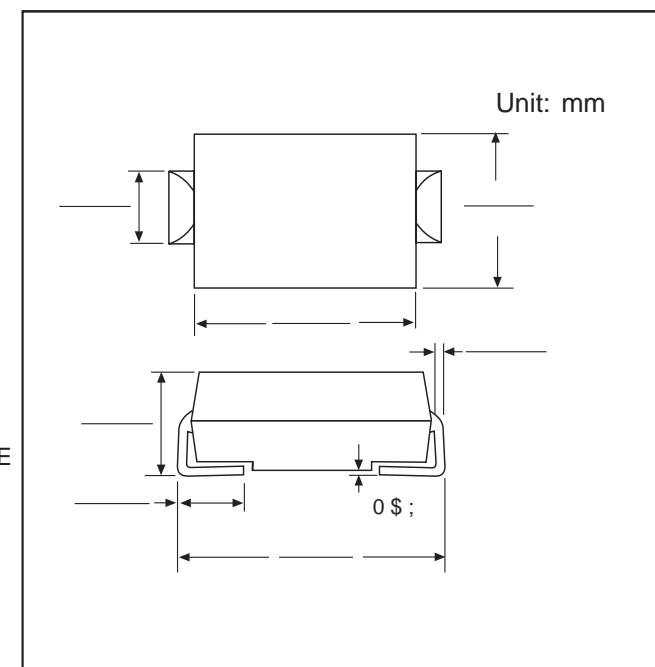
0(&+\$1,&\$/'\$7\$

"Case: SMA molded plastic body

"Polarity:Color band denotes cathode end

"Mounting Position:Any

and WEEE



0\$;,080 5\$7,1*6 \$1' &+\$5\$&7(5,67,&6

f & P E L H Q W S H U D X Q O R H W K H U Z R L W H G

TYPE NUMBER	SYMBOL	SS12	SS13	SS14	SS15	SS16	SS18	SS110	SS115	SS120	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	V
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	105	140	V
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	150	200	V
Maximum Average Forward rectified Current0.375"(9.5mm) lead length	$I_{F(AV)}$	1.0									A
Peak forward surge current8.3ms single half sine-wave superimposed on rated load	I_{FSM}	30.0									A
Maximum instantaneous forward voltage at 1.0 A(Note1)	V_F	0.45	0.55	0.70	0.85						V
Maximum reverse current at rated DC blocking voltage per diode	I_R	0.5									mA
@ $T_A=25$		6.0			5.0						
Typical Thermal Resistance(Note2)	$R_{\theta JA}$	88.0									/W
Typical junction capacitance(Note 3)	C_j	110			90						pF
Storage Temperature	T_{STG}	- ---- + 150									
Operation Junction Temperature	T_j	- 5 ---- + 125			- 5 to +150						

NOTE:

1.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

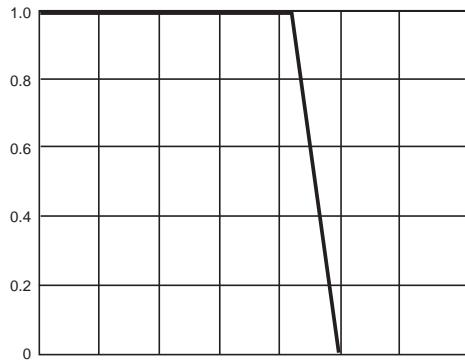
2.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

66 a 66

5 \$ 7 , 1 * 6 \$ 1' & + \$ 5 \$ & 7 (5 , 6 7 , & & 8 5 9 (6

J, *) 2 5 : \$ 5 ' & 8 5 5 (1 7 ' (5 \$ 7 , 1 * & 8 5 9 * 0 \$. , 0 8 0 1 2 1 5 (3 (7 , 7 , 9 (3

) 2 5 : \$ 5 ' 6 8 5 * (& 8 5 5 (1 7



... 3 (\$.) 2 5 : \$ 5 ' 6 8 5 * (& 8 5 5 (6

